

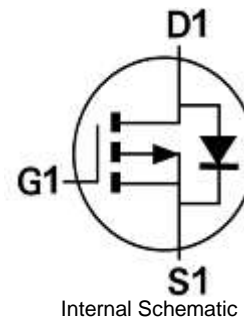
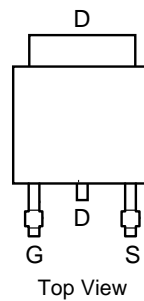
Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D $T_C = +25^\circ C$
-60V	110m Ω @ $V_{GS} = -10V$	-14A
	140m Ω @ $V_{GS} = -4.5V$	-12A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Analog Switch



Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- **Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

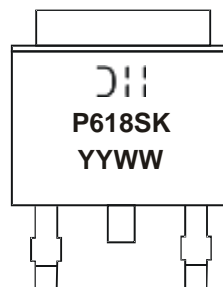
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (Approximate)

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP6180SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
 NH4011SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 16 = 2016)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = -10V	I _D	T _C = +25°C	-14
		T _C = +100°C	-10
Maximum Body Diode Forward Current (Note 7)	I _S	4.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P _D	T _A = +25°C	1.7
		T _A = +70°C	1.0
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	76
		T < 10s	33
Total Power Dissipation (Note 7)	P _D	T _A = +25°C	2.7
		T _A = +70°C	1.5
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	Steady State	50
		t < 10s	24
Total Power Dissipation (Note 7)	P _D	T _C = +25°C	40
		T _C = +100°C	16
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	3.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.2	—	-2.7	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	60	110	mΩ	V _{GS} = -10V, I _D = -12A
		—	80	140		V _{GS} = -4.5V, I _D = -8A
Forward Transfer Admittance	Y _{FS}	—	15	—	S	V _{DS} = -5V, I _D = -12A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	984.7	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	58	—		
Reverse Transfer Capacitance	C _{RSS}	—	45.5	—		
Gate Resistance	R _G	—	12.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _G	—	8.1	—	nC	V _{DS} = -30V, I _D = -12A
Total Gate Charge (V _{GS} = -10V)	Q _G	—	17.1	—		
Gate-Source Charge	Q _{GS}	—	3.2	—		
Gate-Drain Charge	Q _{GD}	—	3.9	—	ns	V _{GS} = -10V, V _{DS} = -30V, R _{GEN} = 3Ω, R _L = 2.5Ω
Turn-On Delay Time	t _{D(ON)}	—	5.9	—		
Turn-On Rise Time	t _R	—	21.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	30.9	—		
Turn-Off Fall Time	t _F	—	39.1	—	ns	I _S = -12A, dI/dt = 100A/µs
Body Diode Reverse Recovery Time	t _{RR}	—	19.9	—		
Body Diode Reverse Recovery Charge	Q _{RR}	—	1.7	—	nC	I _S = -12A, dI/dt = 100A/µs

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout.
 8. Short duration pulse test used to minimize self-heating effect
 9. Guaranteed by design. Not subject to production testing

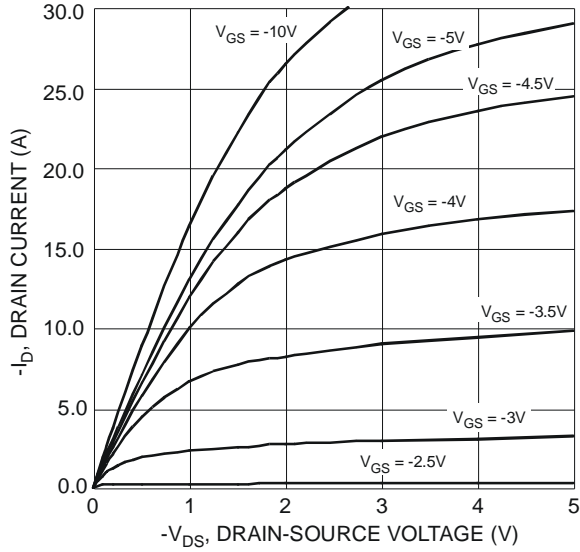


Figure 1 Typical Output Characteristics

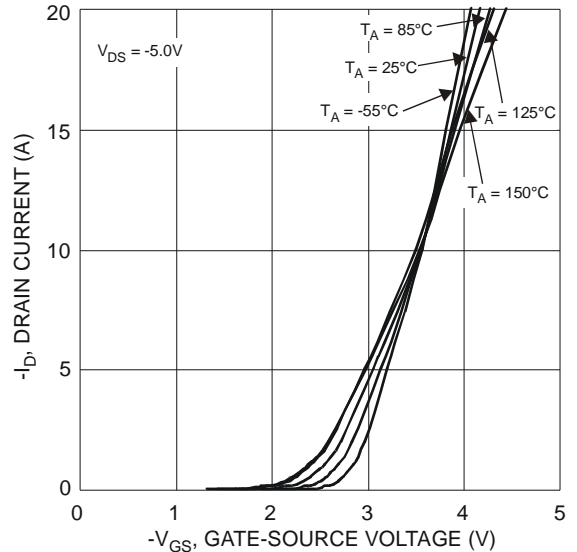


Figure 2 Typical Transfer Characteristics

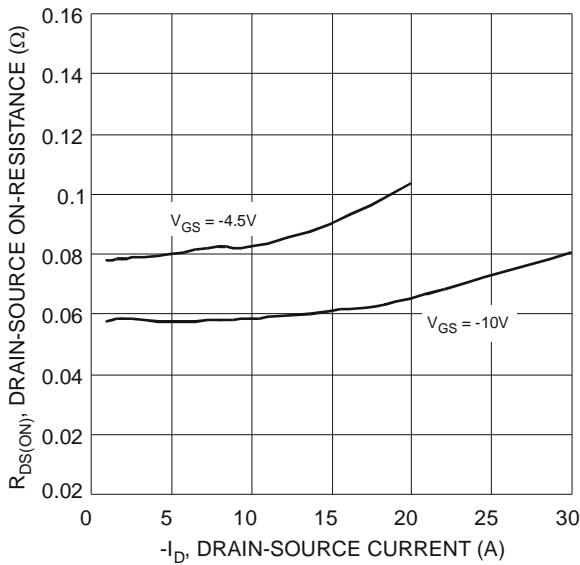


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

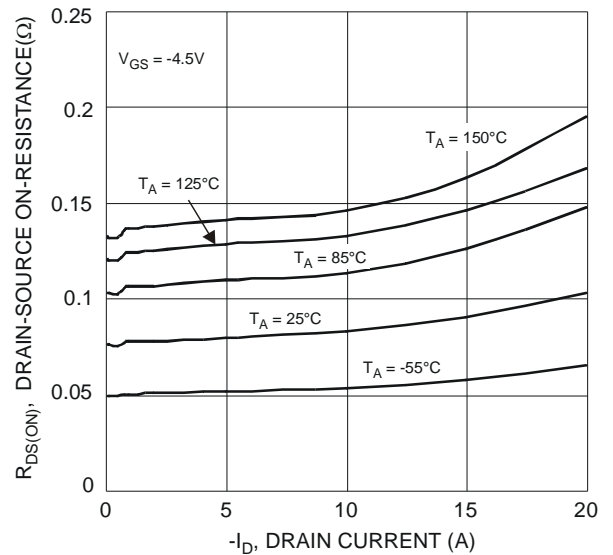


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

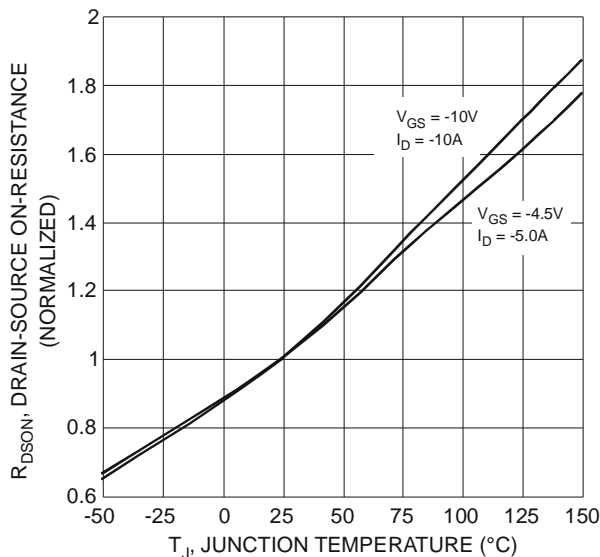


Figure 5 On-Resistance Variation with Temperature

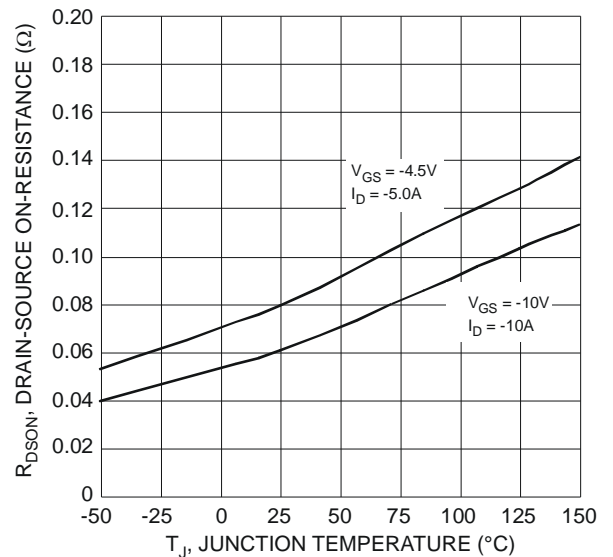


Figure 6 On-Resistance Variation with Temperature

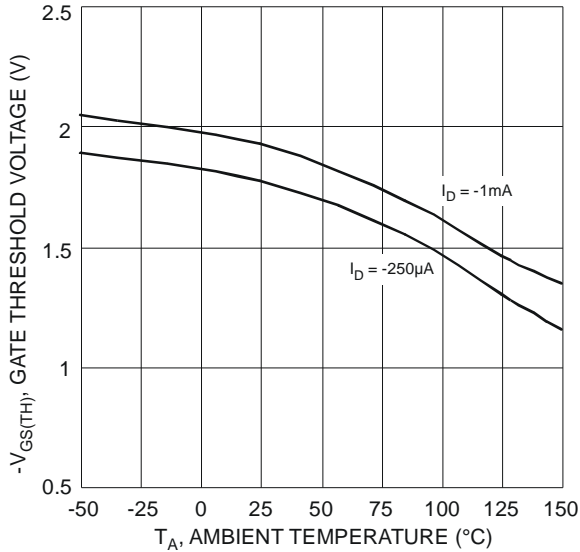


Figure 7 Gate Threshold Variation vs. Ambient Temperature

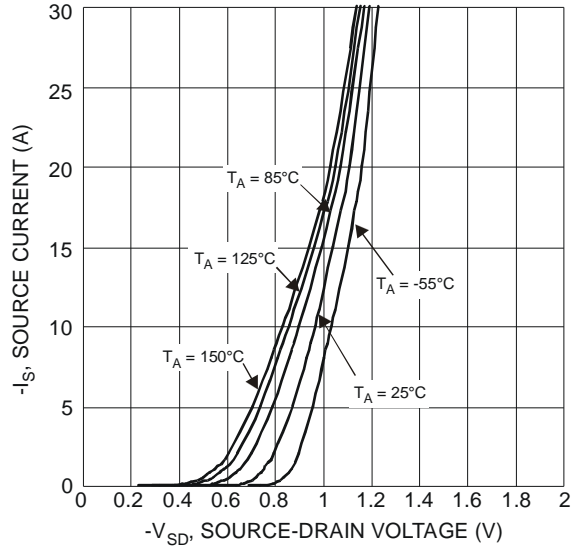


Figure 8 Diode Forward Voltage vs. Current

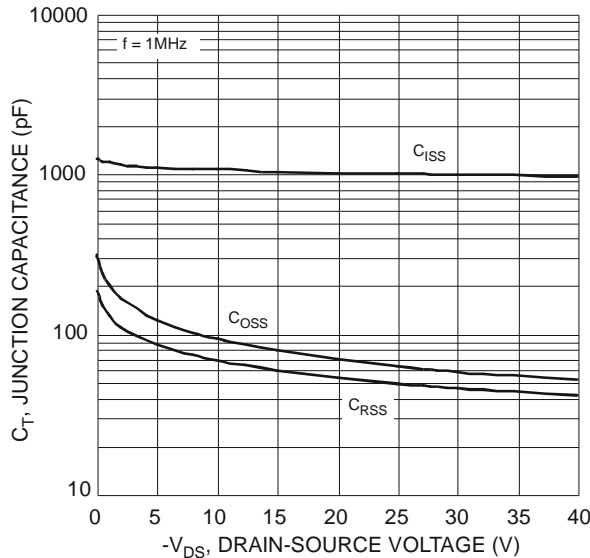


Figure 9 Typical Junction Capacitance

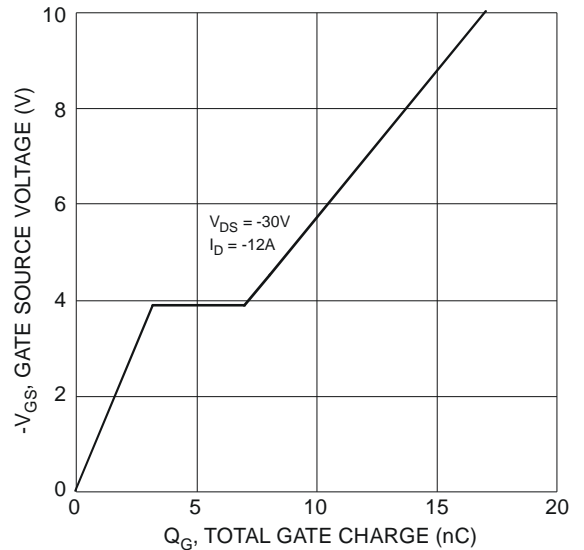


Figure 10 Gate Charge Characteristics

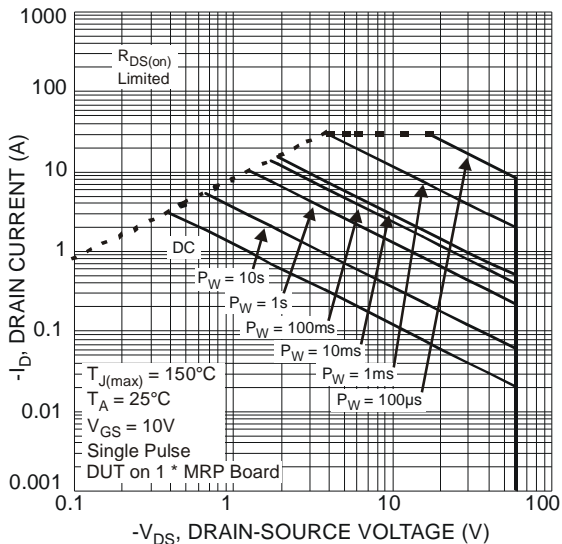


Figure 11 SOA, Safe Operation Area

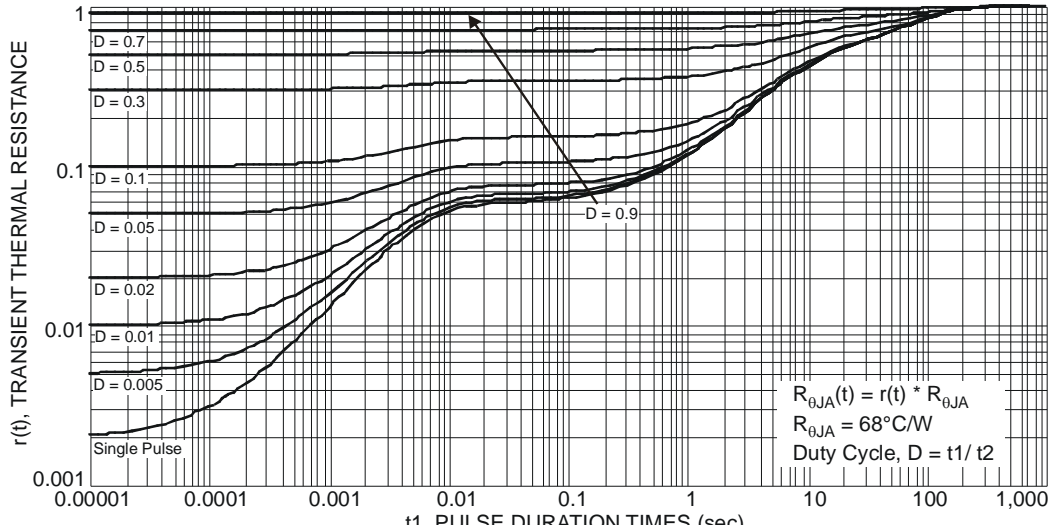
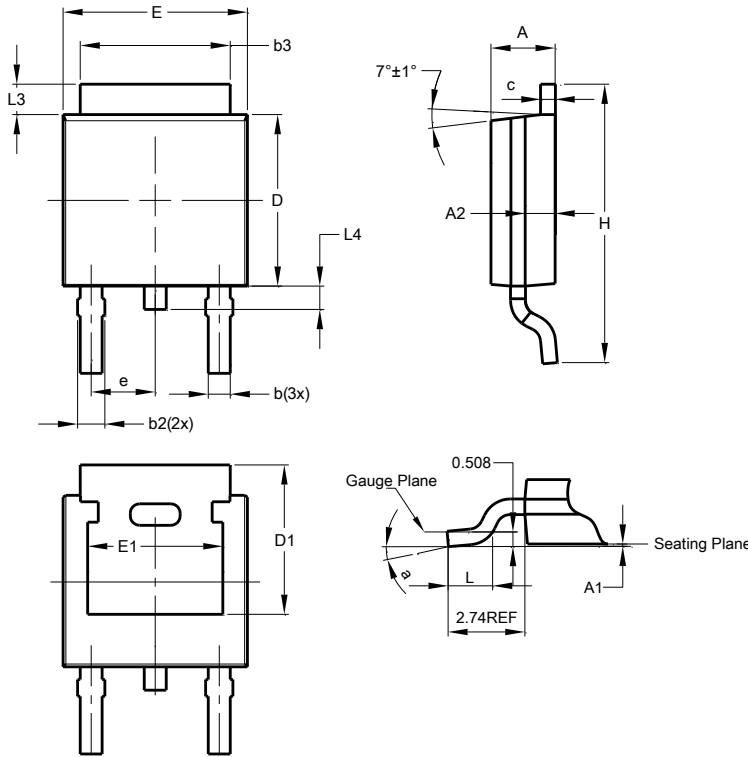


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

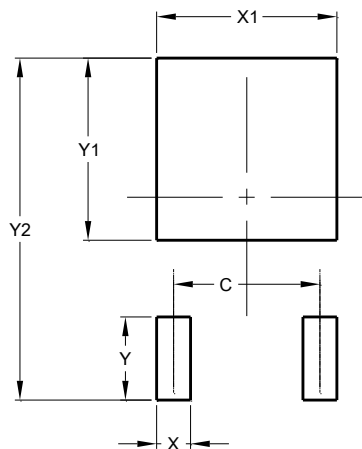


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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